

R&D of atmospheric-pressure µplasma source and its application to material processing

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Keywords		Plasma, Etching, Thin Films Deposition, SiO ₂ , DLC, Water purification, Sterilization			
Technical Support Skills		 R&D of atmospheric-pressure µplasma source and its application to on-site processing Inner wall modification of narrow tubes and microfluidic devices by plasma Decomposition of organic compounds and sterilization in a water by pulsed plasma Material processing technology using a low to high pressure plasma sources 			

Research Contents

1. Material Processing by atmospheric-pressure µplasma

An atmospheric-pressure μ plasma jet source generated at a low power consumption of 1-5 W has been originally developed using a surgical needle with an outer diameter of less than 0.5 mm. Ar, He and also air µplasma jets have easily generated (as shown in **Fig.1**). The µplasma jet was applied to the localized Si etching using SF₆/He/O₂ gases, on-site removal of organic thin films such as polyimide insulator films and local cleaning of terminals of a circuit board.

2. Thin Films Deposition by atmospheric-pressure µplasma

Radio frequency (RF) excited µplasma has been generated inside a narrow tube and a microchannel with an inner diameter of less than 1 mm (as shown in **Fig.2**). The plasma source has been applied to SiO_2 thin films coating on the inner wall of polymer (PTFE and PP) tubes and TiO₂ deposition inside a glass tube. The on-site deposition of diamond-like carbon (DLC) thin films has also been studied using the RF excited μ plasma. Hydrophilic or hydrophobic treatment of a microchannel with a cross section of $350 \times 90 \ \mu$ m² on a commercial microfluidic polymer (COC) chip has been attained by a pulsed discharge.

3. On-site growth of Carbon Nanotubes (CNTs) by atmospheric-pressure µplasma

CNTs have been grown successfully by atmospheric-pressure uplasma chemical vapor deposition with catalyst (Ni) using CH_4/H_2 gas mixture (as shown in **Fig.3**). Field emission (FE) from the vertically grown CNTs bundle was observed. The on-site growth of CNTs will be available to bio-sensor and gas sensor.

4. Water purification and sterilization using a compact plasma bubbler

A compact plasma bubbler made up of a uplasma source and a porous ceramics (Fig.3) has been developed for the applications of water purification and sterilization. Chemical probe method using terephthalic acid revealed that OH radicals are produced by the O_2 plasma gas bubbling. The inactivation for *E. coli*, Bacillus subtilis and Saccharomyces cerevisiae was attained by O₂ and air plasma gas bubbling.

Japan Patent No.5099612 "Water Treatment Device"



Fig.1 AP Ar µplasma jet

Available Facilities and Equipment

Fig.2 RF He µplasma jet

Fig.3 On-site CNTs growth

Fig.4 Plasma gas bubbler

Multichannel Optical Spectrometer (Hamamatsu Photonics PMA-11) UV-Vis Spectrophotometer (Shimadzu UVmini-1240) Quadrupole Mass Spectrometer (Cannon M-101QA-TDM) RF µPlasma Generation System, 13-50 MHz, 30W Microwave Generator, 2.45 GHz, 750 W (Nihon Koshuha)

